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Electronic supplementary information for

## Dramatically enhanced reversibility of Li<sub>2</sub>O in SnO<sub>2</sub>-based electrodes: the effect of nanostructure on high initial reversible capacity

Renzong Hu,<sup>a, b</sup> Dongchang Chen,<sup>b</sup> Gordon Waller,<sup>b</sup> Yunpeng Ouyang,<sup>a</sup> Yu Chen,<sup>b</sup> Bote Zhao,<sup>b</sup> Ben Rainwater,<sup>b</sup> ChenghaoYang,<sup>c</sup> Min Zhu,<sup>\*a</sup> Meilin Liu<sup>\*b, c</sup>

- <sup>a</sup> School of Materials Science and Engineering, South China University of Technology, Guangzhou, 510640, China. E-mail: <u>memzhu@scut.edu.cn</u>
- <sup>b</sup> School of Materials Science and Engineering, Georgia Institute of Technology, Atlanta, GA 30332-0245, USA. E-mail: <u>meilin.liu@mse.gatech.edu</u>
- <sup>c</sup> School of Environment and Energy, South China University of Technology, Guangzhou, 510006, China

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Supplementary figures (Fig.S1-15) and Table (Table S1)



**Fig.S1 (a)** Rietveld refinement XRD for the as-sputtered SnO<sub>2</sub> film. Except those peaks of Cu substrate, all peaks were indexed to single-phase tetragonal (P42/mnm) SnO<sub>2</sub>. From all peaks, crystallite size for SnO<sub>2</sub> is estimated to be 9.45nm, and no microstrain broadening was determined by the fitting, which are in good agreement with Scherer Equation estimation of crystallite size using FWHM of peaks at 26.5° and 33.9° with an average value of 8.85nm. The SnO<sub>2</sub> lattice is nominally tetragonal with a=b=0.4736nm and c=0.3187nm (JCPDS 41-1445). Rietveld refinement of unit cell shows a small compression of the *c* axis and elongation of the *a/b* to *a=b=*0.47507nm and *c=*0.317302nm. Furthermore, a small amount of preferred orientation along *c*-axis to form plates is also observed. (**b**) BET specific surface area of the SnO<sub>2</sub> thin film by N<sub>2</sub>absorption, indicating a very small surface area of  $0.98m^2/g$  for the SnO<sub>2</sub> layer.



Fig.S2 (a) Optical images for the as prepared  $SnO_2$  film, showing the colourless transparent SnO<sub>2</sub> layer.(b) SEM image for the cross-section of the SnO<sub>2</sub> layer, showing its columnar structure with a thickess of around 900nm; (c and d) STEM and dark-field TEM image for a small bundle of SnO<sub>2</sub> scrapped off the Cu substrate, revealing its nano-columnar strucuture and the homogeneous distribution of  $SnO_2$  nanocrystals inside the  $SnO_2$  bundle. (e) Raman data for the SnO<sub>2</sub> film after different treatment in comparison with that of a commercial SnO<sub>2</sub> powder (99% purity, particle size~10µm). Obvious  $A_{1g}$ ,  $B_{2g}$ ,  $E_g$  bands of SnO<sub>2</sub>phase can be found in the as-prepared and Ag-coated SnO<sub>2</sub> film. However, the  $E_g$  band undergoes a blue shift while the  $B_{2g}$ band undergoes a red shift, presumably due to the nano-effects, inner-stress during film growth, and/or the preferred orientation of SnO<sub>2</sub>nanocrystals, because both of them matched well with those of the powder after annealing the film in Ar at 500°C for 4hours. Furthermore, another detectable peak at around 395cm<sup>-1</sup> is present in the annealed SnO<sub>2</sub> film, which could be attributed to structural transformation of the SnO<sub>2</sub> during film annealing. Several peaks at low wave-number portion from 350 to 420 cm<sup>-1</sup> were also frequently found in the nanocrystallineamorphous SnO<sub>2</sub> films (ref.25), and Ag-coated SnO<sub>2</sub> bulk materials(ref.27) due to the multiple optical normal modes of vibrations in SnO<sub>2</sub> lattice. We found that Ag nanoparticles coated on the surface of SnO<sub>2</sub>does not induce obvious change in Raman spectrum. The Ag-coating SnO<sub>2</sub> sample was used for in-situ SERS studies.



**Fig. S3 (a)** XRD patterns of the SnO<sub>2</sub> powder, as-sputtered SnO<sub>2</sub> film, and the film after annealing, indicating that all the visible diffraction peaks in these three samples meet well the tetragonal SnO<sub>2</sub> (JCPDS 41-1445). SEM images for top-view (**b**, **c**) and cross-section (**d**) of the SnO<sub>2</sub> layer after annealing. (**e**) Capacity-potential curves for the first and second cycles, and (f) cycle performance of the annealed SnO<sub>2</sub> film with thickness of 0.9µm.It could be seen that the morphology of the film had been dramatically changed after annealing in Ar at 500°C for 4h. The voids among the macro/micro-columns found in the as-prepared sample have collapsed as the nanosized SnO<sub>2</sub> grains fused to form a dense film. The cross-section image also reveals that as a result of annealing the SnO<sub>2</sub> film layer lost the columnar structure and the boundaries among the nano-columns. Consequently, the annealed film has a much lower initial Coulombic efficiency (70.9%) and inferior capacity retention (60% of the first reversible capacity after 100 cycles) than the film without annealing. These findings help support our original claim that the columnar and porous SnO<sub>2</sub> film morphology is critical for good electrochemical reversibility.



**Fig.S4** SEM images for surface morphology of  $\text{SnO}_2$  film sputtered at different time. (a) 0 second; (b) 18seconds; (c) Magnified SEM image for the surface morphology of film in (b); (d) The first two capacity- potential curves and cycle performance of the 9nm  $\text{SnO}_2$  films. It can be seen that the morphology of the film was dramatically affected by the morphology of Cu substrate because the  $\text{SnO}_2$  layer is too thin. The magnified SEM images show that the film does not present similar microstructure with the  $0.9\mu$ m film, which is lack of the nano-, micro, and macro-column structure and the multi-scale boundary distributions. These also lead to a dense  $\text{SnO}_2$  layer in the thin film. And thus, it yielded quite different electrochemical properties. As we could not determine the accurate mass of  $\text{SnO}_2$  in the 9nm thin film, capacity (mAh) rather than specific capacity (mAh/g) was given. The initial Coulombic efficiency of the 9nm film is 81.7%, with capacity retention of 68.6% after 100 cycles, which are inferior to those of the 0.9um film. This suggests that the unique microstructure, in particular the multi-scale column structure and the boundary distributions, is responsible for the enhanced performance of the 0.9um film.



Fig.S5 (a) Discharge-charge curve and CV curve(inset) of pure Sn thin film, indicating that the lithium storage capacity in Sn mainly comes from the alloying-dealloying reactions at potential below 1.0V vs.Li/Li<sup>+</sup>. (b) The1st discharge-charge curves for four half cells with working electrode used the same SnO<sub>2</sub> film sample. The slight difference on discharge and charge curves, as well as capacity and ICE among these cells could be attributed to the heterogeneous structure in sputtered film. The error in weighing of the punched electrodes and the manual-assembly of the cells could also lead to some variation in the normalized capacities of the electrodes. (c) Comparison the CV curves of SnO<sub>2</sub> film electrode in different electrolytes with different salts and solvents, i.e. LiPF<sub>6</sub> in EC+DEC+FEC, and LiBOB in PC. It can be seen that in both electrolytes, the SnO<sub>2</sub> film electrodes present similar lithiation/delithiation behavior and reversibility. (d and e) CV curves of the SnO<sub>2</sub> film electrode measured with different scanning rates, 0.2,0.3,0.4, and 0.6mV/s, and (f) the relationship between  $I_p$  and  $v^{1/2}$  for peak (1), (2), (3) indicated in (A).Peak (1) is attributed to de-alloying of Li<sub>x</sub>Sn, while peaks (2) and (3) are related to reversing  $Li_2O$  and Sn to SnO<sub>2</sub>. It can be seen that when the scanning rate v increases, the oxidation peaks shift slightly to higher potential with an increase in the peak height. A linear relationship exist between the oxidation peak current of all three peaks and the root of the scan

rate  $(v^{1/2})$ , indicates that the reaction kinetics is controlled by the Li<sup>+</sup> diffusion step. (g) Schematic of the electron and Li<sup>+</sup> conduction pathways in the lithiated SnO<sub>2</sub> electrodes. The Sn and Li<sub>x</sub>Sn nanoparticles would form connected networks in the Li<sub>2</sub>O matrix. The Sn/Li<sub>x</sub>Sn networks serve as conductive paths for electrons, while the Li<sub>2</sub>O provides a similar path for Li<sup>+</sup>. The high fraction of Sn/Li<sub>2</sub>O interface could enhance the kinetics of Li<sup>+</sup> migration in the Li<sub>2</sub>O matrix.



**Fig.S6** *In situ* SERS data for potential (capacity)-lapsed structural evolution of the SnO<sub>2</sub> film electrode during the 1<sup>st</sup> discharge-charge cycle. (**a** and **b**) Discharge from OCP to 0.01V; (**c** and **d**) recharge from 0.01V to 3.0V. The *in situ* SERS data clearly presents the disappearance of SnO<sub>2</sub> and its regeneration along with direct evidence for the formation and decomposition of Li<sub>2</sub>O during discharge and charge by observing the peak at ~520cm<sup>-1</sup>. The weaker intensity at the OCV state in the first cycle was because excess electrolyte was covering the surface of SnO<sub>2</sub>, which will decrease the effective laser intensity illuminating the surface of SnO<sub>2</sub>. During cycling, the electrolyte would permeate the entire cell more comprehensively, which will decrease the thickness of electrolyte layers above the surface of SnO<sub>2</sub>. Therefore, the effective laser power will be increased as cell cycles, leading to increased signal intensity of SnO<sub>2</sub> in the second cycle. Also, it is noted that at the end of charge, the regenerated SnO<sub>2</sub> present narrower band widths in the Raman spectrum. This could be due to that, in some zones, the regenerated nanosizeSnO<sub>2</sub> has a good crystalline and is free of stress and orientation structure.



**Fig.S7** *In situ* SERS data for potential (capacity)-lapsed structural evolution of the  $SnO_2$  film electrode during the 2<sup>nd</sup> discharge-charge cycle. (**a** and **b**) Discharge from OCP to 0.01V; (**c** and **d**) recharge from 0.01V to 3.0V.



**Fig.S8** Microstructure analysis of the SnO<sub>2</sub> film after first discharged to 0.01V. (**a**) Low magnification TEM image and SAED (inset), (**b**) high magnification TEM image, and (**c**) STEM of the SnO<sub>2</sub> film after discharge to 0.01V in the first cycle. The fully lithiated SnO<sub>2</sub> film electrode is unstable even at short exposure of electron beam in TEM. The morphology of the mixture tends to change fast during the exposure to electron beam due to the presence of ultrafine Sn and Li<sub>x</sub>Sn phase with low melting point. There are small holes (dotted circles) appeared in zones focused with electron beam during EELS collection. (**d**) XPS spectra for the Sn 3d levels at various depths of charge-discharge state (pristine, first discharge to 0.01 V (vs. Li/Li<sup>+</sup>), first charge to 3.0V for the SnO<sub>2</sub> film electrodes. In the pristine SnO<sub>2</sub> film, the two strong peaks at ~486.9 and ~495.2 eV, are assigned to Sn 3d<sub>5/2</sub>and 3d<sub>3/2</sub>respectively. After the

film is discharged to 0.01V, these two peaks become much weaker due to the reduction of SnO<sub>2</sub>. In addition, they shifted by about 0.5eV toward lower binding energies. This shift could be explained by the formation of the Li<sub>x</sub>Sn alloy according to reference. However, the XPS signal of the Li<sub>x</sub>Sn phase was not very strong at the fully lithiated SnO<sub>2</sub>, which might be attributed to the embedded Li<sub>x</sub>Sn in the amorphous Li<sub>2</sub>O matrix and the coverage of the SEI layer. In addition, as the fully lithiated SnO<sub>2</sub> sample is highly sensitive to air, thus the Li<sub>x</sub>Sn and Sn could be quickly oxidized to formed thin SnO<sub>2</sub> layer on the near surface during the film transfer from the Ar-filled glove box to the XPS. Nevertheless, the characteristic XPS peaks for SnO<sub>2</sub>became stronger after the electrode is recharged to 3.0 V (vs. Li/Li<sup>+</sup>), with the same binding energies for Sn 3d<sub>5/2</sub> and 3d<sub>3/2</sub> as in the as-sputtered film. Fitting of the Sn 3d<sup>5/2</sup> XPS also suggested that the SnO<sub>2</sub> is the dominant phase in the charged film. These confirm that the matrix Li<sub>2</sub>O could react with newly formed metallic Sn to yield SnO<sub>2</sub> during charge. This is in agreement with the *ex situ* XRD and the *in situ* SERS results.



**Fig.S9** Fitting of the Sn  $3d^{5/2}$  XPS of the SnO<sub>2</sub> film at different depths of charge- discharge state: (a) pristine, (b) first discharged to 0.01 V (vs. Li/Li<sup>+</sup>), (c) first charged to 3.0V (vs. Li/Li<sup>+</sup>), suggesting that the SnO<sub>2</sub> is the dominant phase in the charged film.



**Fig.S10** Schematic drawing, optical images showing the spectroelectrochemical cell configuration and operation for in-situ SERS testing. The cells, with liquid state electrolyte of LiBOB in PC, were assembled in Ar-filled glovebox.



**Fig.S11** (a) Comparison of the Raman spectrum of  $SnO_2$  thin film in LiPF<sub>6</sub> based electrolyte and LiBOB-based electrolyte, showing that there was serious fluorescence effect in case of LiPF<sub>6</sub> based electrolyte, which covered all the signals of  $SnO_2$ . The Raman spectrum at OCP shows lower peak intensity for  $SnO_2$  due to the covering of electrolyte and Ag nanoparticles on the film surface. (b) Raman data from the  $SnO_2$  film electrode at the end of 1<sup>st</sup>discharge to 0.01V in 1M LiBOB–PC showing obvious Li<sub>2</sub>O formation, which has similar spectrum to that collected for the oxide surface of Li foil. Previous reports indicate that Li<sub>2</sub>O is not evident in *insitu* XRD, or *insitu* TEM due to its poor crystallinity in the lithiated  $SnO_2$  electrode. In addition, Li<sub>2</sub>O is sensitive to air and moisture, thus it is necessary to use techniques such as *insitu* SERS to observe its formation and decomposition in electrochemical cells. The Raman spectrum of LiBOB also has three detectable peaks, however at different regions of the Raman spectrum in comparison with those of  $SnO_2$  and Li<sub>2</sub>O.



**Fig.S12** Optical images for the  $SnO_2$  film electrode at different potential states during the 1<sup>st</sup> discharge-charge cycle. They were recorded by the CCD camera coupled with the Raman systemduring collection of the *insitu* SERS data, showing the volume variation and surface mophology change of the film during Li<sup>+</sup> insertion and extraction.



**Fig .S13** SEM image (**a**) and enlarged SEM image(**b**) of another sputtered  $SnO_2$  film (sample 2),using the same power(150W, 30min) and working gas pressure(2.0Pa)as those for sample 1 which was discussed in detail for this work, however sample 2 was produced with continuous rotation for the Cu substrate during sputtering. It can be found that sample 2 is much denser and without the obvious three structural units: nano-, micro-, and macro-columns, together with associated nano-, micro, and macro-void distributions; (**c** and **d**) comparison of the 1<sup>st</sup>discharge-charge curves, differential charge capacities for the two  $SnO_2$  film samples, indicating that the sample 1 presents much better reversibility of lithiation /delithiation and thus much higher ICE.



**Fig .S14** (a) Comparison of *exsitu* XRD partterns for the SnO<sub>2</sub> electrode recharged to 1.2V after different cycle numbers(1<sup>st</sup>, 2<sup>nd</sup>, 6<sup>th</sup>, 12<sup>th</sup>); (b) The full width at half maximum(FWHM) for Sn (101) diffraction peak *vs.* cycle number. The gradually decrease of FWHM indicates the coarsening of Sn crystals during cycling.



**Fig.S15** Schematic diagram for a Li-O<sub>2</sub> battery. The cathode is designed to have a hierarchical construction for porous carbon and its loading metal and/or oxides catalysts, where the catalysts mainly disperse on the inner surfaces of multi-scale carbon pores rather than inside the carbon frameworks. During discharge, O<sub>2</sub> react with Li<sup>+</sup> in pores to form Li<sub>2</sub>O mainly on the surfaces of catalyst. Due to direct contact with the well selected catalyst and the Li<sub>2</sub>O phase formed during discharge, the decomposition of Li<sub>2</sub>O could be complete at modest potential ranges during charge. This hierarchical structure is expected to maintain fast transport of O<sub>2</sub> and good contact between Li<sup>+</sup>, Li<sub>2</sub>O and catalysts in O<sub>2</sub>cathode during Li-O<sub>2</sub> battery operation.

Reaction /materials	D <sub>Li+</sub> (m²/s)	References
(peak 1) Li <sub>x</sub> Sn—Li <sup>+</sup> +Sn	1 x 10 <sup>-11</sup>	This work
(peak 2, 3) $Li_2O+Sn-Li^++SnO_2$	6 x 10 <sup>-13</sup>	This work
Li <sub>2</sub> O in lithiatedSnO <sub>2</sub> single nanowire	5 x 10 <sup>-16~</sup> 5 x 10 <sup>-14</sup>	Ref.14
lithiated amorphous SnO <sub>2</sub> thin film	10 <sup>-15</sup> ~10 <sup>-13</sup>	Ref. 23

Table S1 Diffusion coefficient of Li<sup>+</sup> in different kinds of lithiated SnO<sub>2</sub> materials

Based on the CV results shown in Fig.S5, we can determine the diffusivity of Li<sup>+</sup> during the reaction by the following equation,

$$I_p = 2.69 \times 10^5 A n^{3/2} C_0 D^{1/2} v^{1/2}$$

Where *n* is the number of electrons per molecules during the intercalation (Li<sup>+</sup>, n=1), *A* is the surface area of the electrode (0.317cm<sup>2</sup> in this work),  $C_0$  is the initial concentration of lithium ions (1mol/L in electrolyte). *D* is the diffusion coefficient of Li<sup>+</sup>. On the basis of our data, the  $D_{\text{Li}+}$  in different reactions were calculated and listed in **Table S1** below, compared with that of in other lithiated SnO<sub>2</sub> materials.

The diffusion distance (*l*) of Li<sup>+</sup> during the time (at 1/5C rate) for reverse reaction of Li<sub>2</sub>O to  $SnO_2$ , i.e. decomposition of  $SnO_2$  among potential range of 1.0-3.0V (take about 8000s), was approximately evaluated by the following equation:

$$l=\sqrt{Dt}$$

Accordingly, a diffusion distance over  $70\mu m$ , much larger than thickness of the SnO<sub>2</sub> layer in film, could be achieved during the Li<sub>2</sub>O reversion step.